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	APPLICANT: Hans Joachim Müssig	
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UNITED STATES PATENT DOCUMENTS

EXAM. INITIAL		DOCUMENT NUMBER	ISSUE/PUBL DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MDH	US	2002/0036313	3-28-2002	Sam Yang et al.	—	—	—
	US	2003/0228747	12-11-2003	Kie Y. Ahn et al.	—	—	—
	US	6,656,852	12-2-2003	Antonio Luis Pacheco Rotondaro et al.	—	—	—
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↓	US	2003/0193061	10-16-2003	Hans-Jörg Osten	—	—	—

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		DOCUMENT NUMBER	DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	TRANSLATION YES/NO
MDH	WO	02/097895	12-5-2002	Dietmar Krüger et al.	—	—	abstract only

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

MDH	Surface Science 504 (2002) 159-166, XP-001189099, Initial stages of praseodymium oxide film formation on Si(001), H.-J. Müssig et al., IHP, Im Technologiepark 25, D-15236 Frankfurt (Oder), Germany; received 8 September 2001, accepted for publication 3 Dec. 2001.
MDH	2001 IRW Final Report, 0-7803-7167-4/01/2001 IEEE, Can Praseodymium Oxide be an Alternative High-K Gate Dielectric Material for Silicon Integrated Circuits?, H. -J Müssig et al., IHP, Im Technologiepark 25, D-15236 Frankfurt (Oder), Germany.
Examiner <i>Marcus D. Rimmer</i>	Date: <i>August 24, 2005</i>